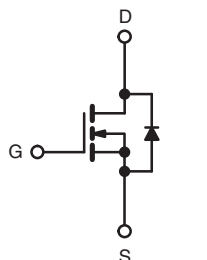
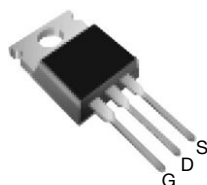


D Series Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	450	
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V	0.17
Q_g max. (nC)	88	
Q_{gs} (nC)	12	
Q_{gd} (nC)	23	
Configuration	Single	

TO-220AB


N-Channel MOSFET

FEATURES

- Optimal Design
 - Low Area Specific On-Resistance
 - Low Input Capacitance (C_{iss})
 - Reduced Capacitive Switching Losses
 - High Body Diode Ruggedness
 - Avalanche Energy Rated (UIS)
- Optimal Efficiency and Operation
 - Low Cost
 - Simple Gate Drive Circuitry
 - Low Figure-of-Merit (FOM): $R_{on} \times Q_g$
 - Fast Switching
- Compliant to RoHS Directive 2011/65/EU

Note

* Pb containing terminations are not RoHS compliant, exemptions may apply

APPLICATIONS

- Consumer Electronics
 - Displays (LCD or Plasma TV)
- Lighting
- Industrial
 - Welding
 - Induction Heating
 - Motor Drives
 - Battery Chargers
- SMPS



RoHS*
COMPLIANT
HALOGEN
FREE
Available

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	SiHP25N40D-E3
Lead (Pb)-free and Halogen-free	SiHP25N40D-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	400	V
Gate-Source Voltage	V_{GS}	± 30	
Gate-Source Voltage AC ($f > 1$ Hz)		30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current ^a	I_{DM}	78	
Linear Derating Factor		2.2	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	556	mJ
Maximum Power Dissipation	P_D	278	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C
Drain-Source Voltage Slope	dV/dt	24	V/ns
Reverse Diode dV/dt ^d		0.6	
Soldering Recommendations (Peak Temperature)	for 10 s	300°	°C

Notes

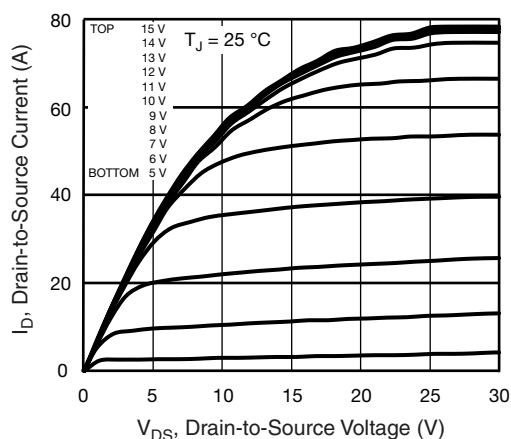
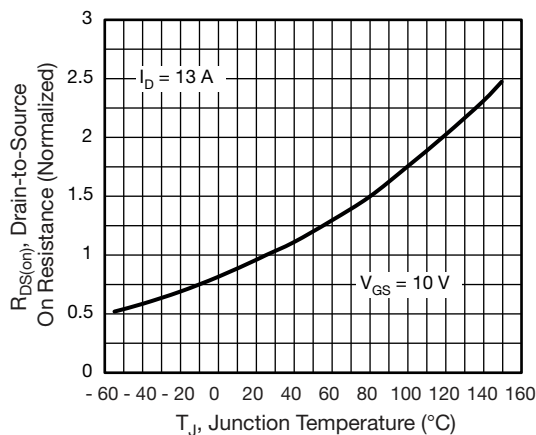
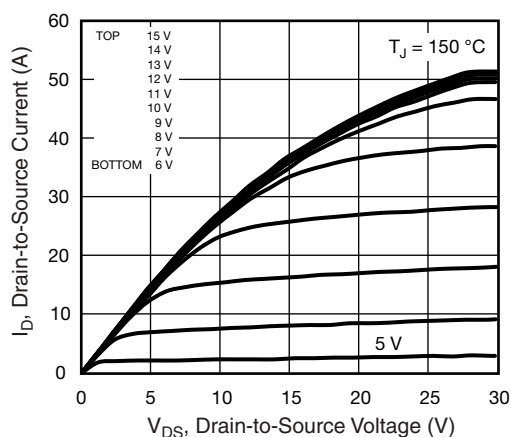
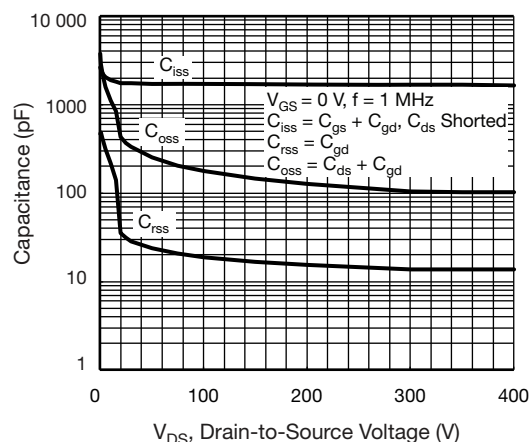
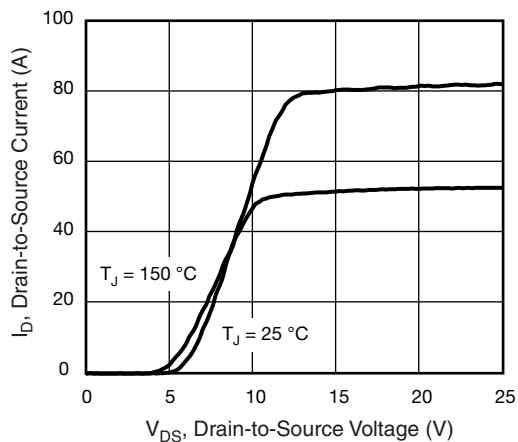
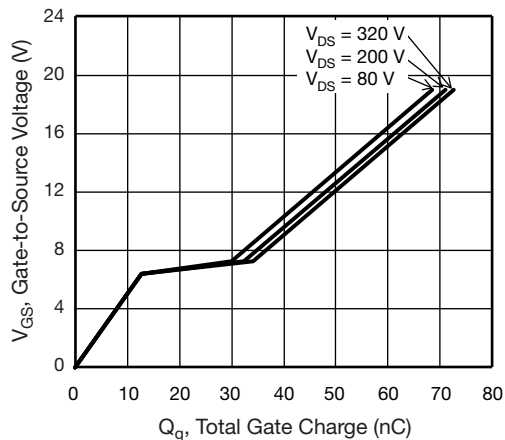
- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 2.3$ mH, $R_g = 25$ Ω , $I_{AS} = 17$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, starting $T_J = 25$ °C.

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.45	

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	400	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C , $I_D = 250\text{ }\mu\text{A}$	-	0.5	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	-	5	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 320\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ °C}$	-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 13\text{ A}$	-	0.14	0.17	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 13\text{ A}$	-	7.4	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$	-	1707	-	pF
Output Capacitance	C_{oss}		-	177	-	
Reverse Transfer Capacitance	C_{rss}		-	19	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 13\text{ A}$, $V_{DS} = 320\text{ V}$	-	44	88	nC
Gate-Source Charge	Q_{gs}		-	12	-	
Gate-Drain Charge	Q_{gd}		-	23	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 320\text{ V}$, $I_D = 13\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 24.6\text{ }\Omega$	-	21	42	ns
Rise Time	t_r		-	57	86	
Turn-Off Delay Time	$t_{d(off)}$		-	40	80	
Fall Time	t_f		-	37	74	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain	-	1.8	-	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	24	A
Pulsed Diode Forward Current	I_{SM}		-	-	78	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ °C}$, $I_S = 13\text{ A}$, $V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ °C}$, $I_F = I_S = 13\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 20\text{ V}$	-	353	-	ns
Reverse Recovery Charge	Q_{rr}		-	4.4	-	μC
Reverse Recovery Current	I_{RRM}		-	24	-	A

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

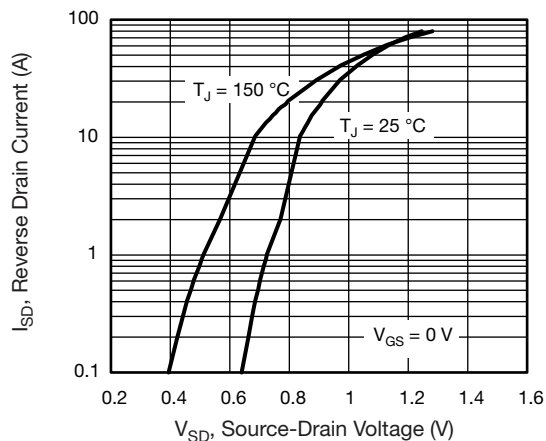
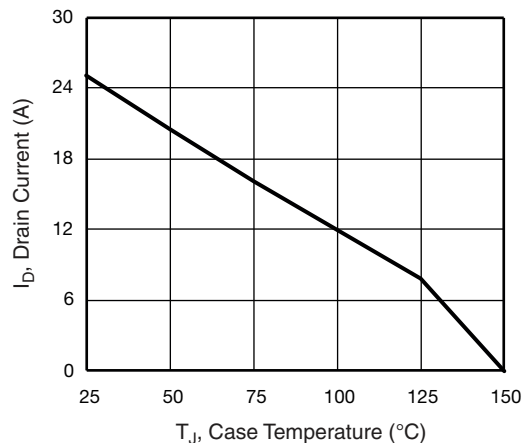
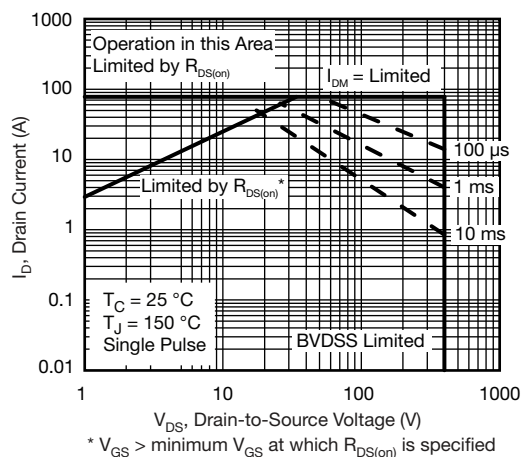
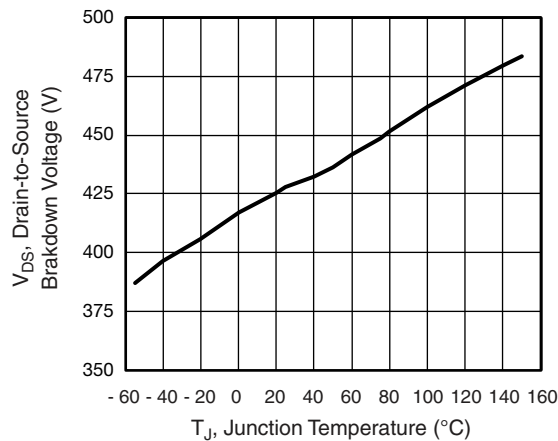
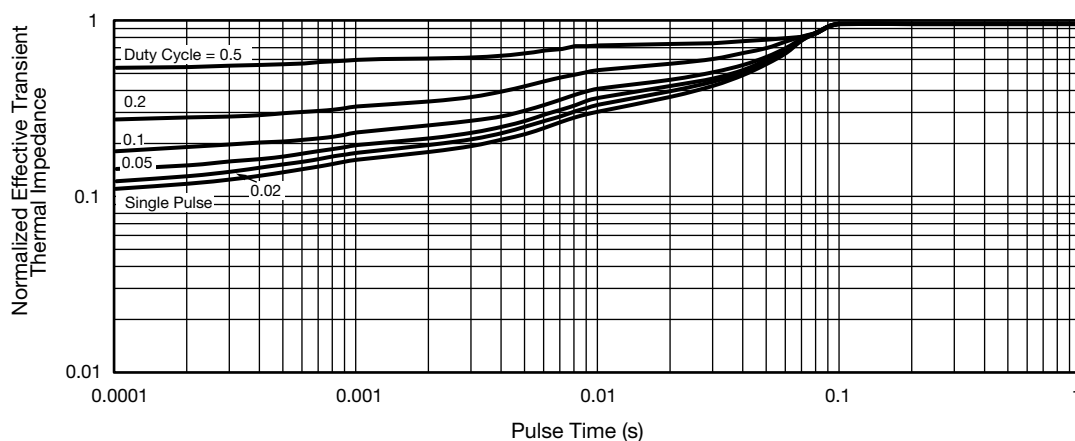

Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Maximum Safe Operating Area

Fig. 10 - Temperature vs. Drain-to-Source Voltage

Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case


Fig. 12 - Switching Time Test Circuit

Fig. 16 - Basic Gate Charge Waveform

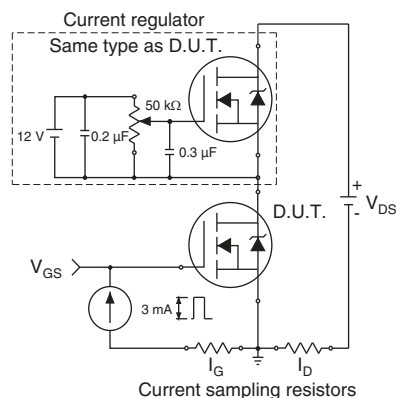
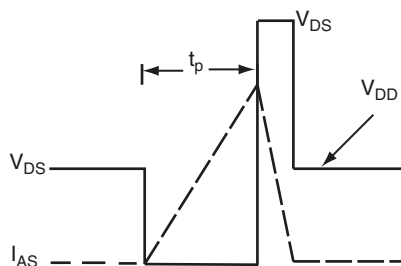
Fig. 13 - Switching Time Waveforms

Fig. 17 - Gate Charge Test Circuit

Fig. 14 - Unclamped Inductive Test Circuit

Fig. 15 - Unclamped Inductive Waveforms


Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

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